

AMENDMENTS**In the specification**

On page 8, please amend the paragraph beginning on line 15 as follows:

The second-conductivity-type clad layer is suitably a semiconductor layer containing, for example, Al, Ga, As, In and/or P as constituent atoms. More specifically, it is preferable that the clad layer be formed of $(\text{Ga}_{1-y}\text{Al}_y)_m\text{In}_{1-m}\text{P}$ (wherein, for example, $y=0.7$, $m=0.5$, though ~~x and z~~ y and m may be such that $0.1 \leq y \leq 0.9$, and $0.2 \leq m \leq 0.8$). In the case where the active layer is formed of GaAlInP and the second-conductivity-type clad layer is also formed of GaAlInP, it is preferable that the Al mixed crystal ratio of the active layer be lower than that of the second-conductivity-type clad layer. More specifically, the Al mixed crystal ratio of the second-conductivity-type clad layer may be about 0.5 to 0.9 and, more preferably, about 0.7. The concentration of impurities in the second-conductivity-type clad layer is suitably, for example, in the range of about 1×10^{17} to $4 \times 10^{17} \text{ cm}^{-3}$. The thickness of the clad layer is suitably, for example, about 0.7 to 1.0 μm .